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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	50
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.85V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TQFP
Supplier Device Package	64-TQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg332f512-qfp64t

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M3, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32GG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32GG332 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32GG Reference Manual*.

A block diagram of the EFM32GG332 is shown in Figure 2.1 (p. 3) .



Figure 2.1. Block Diagram

2.1.1 ARM Cortex-M3 Core

The ARM Cortex-M3 includes a 32-bit RISC processor which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Memory Protection Unit with support for up to 8 memory segments is included, as well as a Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep. The EFM32 implementation of the Cortex-M3 is described in detail in *EFM32 Cortex-M3 Reference Manual*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface and an Embedded Trace Module (ETM) for data/instruction tracing. In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

2.1.18 Low Energy Timer (LETIMER)

The unique LETIMERTM, the Low Energy Timer, is a 16-bit timer that is available in energy mode EM2 in addition to EM1 and EM0. Because of this, it can be used for timing and output generation when most of the device is powered down, allowing simple tasks to be performed while the power consumption of the system is kept at an absolute minimum. The LETIMER can be used to output a variety of waveforms with minimal software intervention. It is also connected to the Real Time Counter (RTC), and can be configured to start counting on compare matches from the RTC.

2.1.19 Pulse Counter (PCNT)

The Pulse Counter (PCNT) can be used for counting pulses on a single input or to decode quadrature encoded inputs. It runs off either the internal LFACLK or the PCNTn_S0IN pin as external clock source. The module may operate in energy mode EM0 - EM3.

2.1.20 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.21 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.22 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 8 external pins and 6 internal signals.

2.1.23 Digital to Analog Converter (DAC)

The Digital to Analog Converter (DAC) can convert a digital value to an analog output voltage. The DAC is fully differential rail-to-rail, with 12-bit resolution. It has two single ended output buffers which can be combined into one differential output. The DAC may be used for a number of different applications such as sensor interfaces or sound output.

2.1.24 Operational Amplifier (OPAMP)

The EFM32GG332 features 3 Operational Amplifiers. The Operational Amplifier is a versatile general purpose amplifier with rail-to-rail differential input and rail-to-rail single ended output. The input can be set to pin, DAC or OPAMP, whereas the output can be pin, OPAMP or ADC. The current is programmable and the OPAMP has various internal configurations such as unity gain, programmable gain using internal resistors etc.

2.1.25 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface (LESENSETM), is a highly configurable sensor interface with support for up to 4 individually configurable sensors. By controlling the analog comparators and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable FSM which enables simple processing of measurement results without CPU intervention. LESENSE is

3.4.3 EM4 Current Consumption





3.5 Transition between Energy Modes

The transition times are measured from the trigger to the first clock edge in the CPU.

Table 3.4. Energy Modes Transitions

Symbol	Parameter	Min	Тур	Max	Unit
tem10	Transition time from EM1 to EM0		0		HF- CORE- CLK cycles
t _{EM20}	Transition time from EM2 to EM0		2		μs
t _{EM30}	Transition time from EM3 to EM0		2		μs
t _{EM40}	Transition time from EM4 to EM0		163		μs

3.6 Power Management

The EFM32GG requires the AVDD_x, VDD_DREG and IOVDD_x pins to be connected together (with optional filter) at the PCB level. For practical schematic recommendations, please see the application note, "AN0002 EFM32 Hardware Design Considerations".



Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Тур	Max	Unit
	BOD threshold on	EMO	1.74		1.96	V
VBODextthr-	ply voltage	EM2	1.74		1.98	V
V _{BODintthr} -	BOD threshold on falling internally reg- ulated supply volt- age		1.57		1.70	V
V _{BODextthr+}	BOD threshold on rising external sup- ply voltage			1.85	1.98	V
V _{PORthr+}	Power-on Reset (POR) threshold on rising external sup- ply voltage				1.98	V
t _{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		μs
C _{DECOUPLE}	Voltage regulator decoupling capaci-tor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		μF
C _{USB_VREGO}	USB voltage regu- lator out decoupling capacitor.	X5R capacitor recommended. Apply between USB_VREGO pin and GROUND		1		μF
C _{USB_VREGI}	USB voltage regula- tor in decoupling ca- pacitor.	X5R capacitor recommended. Apply between USB_VREGI pin and GROUND		4.7		μF

3.7 Flash

Table 3.6. Flash

Symbol	Parameter	Condition	Min	Тур	Max	Unit
EC _{FLASH}	Flash erase cycles before failure		20000			cycles
		T _{AMB} <150°C	10000			h
RET _{FLASH}	Flash data retention	T _{AMB} <85°C	10			years
		T _{AMB} <70°C	20			years
t _{W_PROG}	Word (32-bit) pro- gramming time		20			μs
+	Page erase time	LPERASE == 0	20	20.4	20.8	ms
PERASE		LPERASE == 1	40	40.4	40.8	ms
t _{DERASE}	Device erase time				161.6	ms
	Eraso ourront	LPERASE == 0			14 ¹	mA
'ERASE	Erase current	LPERASE == 1			7 ¹	mA
	Write ourrept	LPWRITE == 0			14 ¹	mA
WRITE	white current	LPWRITE == 1			7 ¹	mA
V _{FLASH}	Supply voltage dur- ing flash erase and write		1.98		3.8	V

¹Measured at 25°C

3.8 General Purpose Input Output

Table 3.7. GPIO

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
V _{IOIL}	Input low voltage				0.30V _{DD}	V
V _{IOIH}	Input high voltage		0.70V _{DD}			V
		Sourcing 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V _{DD}		V
	Output high volt- age (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V _{DD}		V
		Sourcing 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V _{DD}		V
VIOOH		Sourcing 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V _{DD}		V
		Sourcing 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V _{DD}			V
		Sourcing 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V _{DD}			V



Symbol	Parameter	Condition	Min	Тур	Max	Unit
		Sourcing 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V _{DD}			V
		Sourcing 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V _{DD}			V
		Sinking 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V _{DD}		V
		Sinking 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V _{DD}		V
Vicei	Output low voltage (Production test	Sinking 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V _{DD}		V
VIOOL	condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V _{DD}	V
		Sinking 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V _{DD}	V
		Sinking 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V _{DD}	V
		Sinking 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.20V _{DD}	V
I _{IOLEAK}	Input leakage cur- rent	High Impedance IO connected to GROUND or V_{DD}		±0.1	±40	nA
R _{PU}	I/O pin pull-up resis- tor			40		kOhm
R _{PD}	I/O pin pull-down re- sistor			40		kOhm
R _{IOESD}	Internal ESD series resistor			200		Ohm
t _{IOGLITCH}	Pulse width of puls- es to be removed by the glitch sup- pression filter		10		50	ns
tioor	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOWEST and load capaci- tance C_L =12.5-25pF.	20+0.1C _L		250	ns
VIOOL IIOLEAK RPU RPD RIOESD tIOGLITCH tIOOF		$\begin{array}{l} GPIO_{Px} CTRL \; DRIVEMODE \\ = \; LOW \; and \; load \; capacitance \\ C_{L} = 350- 600pF \end{array}$	20+0.1C _L		250	ns
V _{IOHYST}	I/O pin hysteresis (V _{IOTHR+} - V _{IOTHR-})	V _{DD} = 1.98 - 3.8 V	0.10V _{DD}			V



Figure 3.6. Typical Low-Level Output Current, 3V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = STANDARD





GPIO_Px_CTRL DRIVEMODE = HIGH



Figure 3.7. Typical High-Level Output Current, 3V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = STANDARD

GPIO_Px_CTRL DRIVEMODE = HIGH



Figure 3.8. Typical Low-Level Output Current, 3.8V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = HIGH



Figure 3.16. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature



3.9.5 AUXHFRCO

Table 3.12. AUXHFRCO

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
		28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
f	Oscillation frequen-	14 MHz frequency band	13.7	14.0	14.3	MHz
IAUXHFRCO	cy, v _{DD} = 3.0 v, T _{AMB} =25°C	11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48 ¹	6.60 ¹	6.72 ¹	MHz
1		1 MHz frequency band	1.15 ²	1.20 ²	1.25 ²	MHz
t _{AUXHFRCO_settlir}	_g Settling time after start-up	f _{AUXHFRCO} = 14 MHz		0.6		Cycles
DC _{AUXHFRCO}	Duty cycle	f _{AUXHFRCO} = 14 MHz	48.5	50	51	%
TUNESTEP _{AU>} HFRCO	Frequency step for LSB change in TUNING value			0.3 ³		%

¹For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

 2 For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

³The TUNING field in the CMU_AUXHFRCOCTRL register may be used to adjust the AUXHFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the AUXHFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

3.9.6 ULFRCO

Table 3.13. ULFRCO

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
f _{ULFRCO}	Oscillation frequen- cy	25°C, 3V	0.70		1.75	kHz
TC _{ULFRCO}	Temperature coeffi- cient			0.05		%/°C
VC _{ULFRCO}	Supply voltage co- efficient			-18.2		%/V

3.10 Analog Digital Converter (ADC)

Table 3.14. ADC

Symbol	Parameter	Condition	Min	Тур	Max	Unit
		Single ended	0		V _{REF}	V
V ADCIN	input voltage range	Differential	-V _{REF} /2		V _{REF} /2	V
V _{ADCREFIN}	Input range of exter- nal reference volt- age, single ended and differential		1.25		V _{DD}	V
V _{ADCREFIN_CH7}	Input range of ex- ternal negative ref- erence voltage on channel 7	See V _{ADCREFIN}	0		V _{DD} - 1.1	V
V _{ADCREFIN_CH6}	Input range of ex- ternal positive ref- erence voltage on channel 6	See V _{ADCREFIN}	0.625		V _{DD}	V
	Common mode in- put range		0		V _{DD}	V
	Input current	2pF sampling capacitors		<100		nA
CMRR _{ADC}	Analog input com- mon mode rejection ratio			65		dB
		1 MSamples/s, 12 bit, external reference		351		μΑ
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP- MODE in ADCn_CTRL set to 0b00		67		μA
I _{ADC}	Average active cur- rent	10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP- MODE in ADCn_CTRL set to 0b01		63		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP- MODE in ADCn_CTRL set to 0b10		64		μA
I _{ADCREF}	Current consump- tion of internal volt- age reference	Internal voltage reference		65		μA

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Symbol	Parameter	Condition	Min	Тур	Max	Unit
C _{ADCIN}	Input capacitance			2		pF
R _{ADCIN}	Input ON resistance		1			MOhm
R _{ADCFILT}	Input RC filter resis- tance			10		kOhm
C _{ADCFILT}	Input RC filter/de- coupling capaci- tance			250		fF
f _{ADCCLK}	ADC Clock Fre- quency				13	MHz
		6 bit	7			ADC- CLK Cycles
t _{ADCCONV}	Conversion time	8 bit	11			ADC- CLK Cycles
		12 bit	13			ADC- CLK Cycles
t _{ADCACQ}	Acquisition time	Programmable	1		256	ADC- CLK Cycles
t _{ADCACQVDD3}	Required acquisi- tion time for VDD/3 reference		2			μs
	Startup time of ref- erence generator and ADC core in NORMAL mode			5		μs
tadcstart	Startup time of ref- erence generator and ADC core in KEEPADCWARM mode			1		μs
		1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		65		dB
SNRADC	Signal to Noise Ra-	1 MSamples/s, 12 bit, differen- tial, internal 1.25V reference		60		dB
	10 (JNK)	1 MSamples/s, 12 bit, differen- tial, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differen- tial, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		69		dB



Symbol	Parameter	Condition	Min	Тур	Max	Unit
		200 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V _{DD} reference		67		dB
		200 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	63	66		dB
		200 kSamples/s, 12 bit, differ- ential, 2xV _{DD} reference		70		dB
		1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		58		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		62		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		64		dB
		1 MSamples/s, 12 bit, differen- tial, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differen- tial, internal 2.5V reference		64		dB
		1 MSamples/s, 12 bit, differen- tial, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		66		dB
SINAD _{ADC}	SIgnal-to-Noise And Distortion-ratio (SINAD)	1 MSamples/s, 12 bit, differen- tial, 2xV _{DD} reference		68		dB
		200 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		61		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		65		dB
		200 kSamples/s, 12 bit, single ended, V _{DD} reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differ- ential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	62	65		dB

3.10.1 Typical performance

Figure 3.19. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°C





Symbol	Parameter	Condition	Min	Тур	Max	Unit
		500 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		58		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		59		dB
SNDR _{DAC}		500 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		57		dB
	Signal to Noise-	500 kSamples/s, 12 bit, single ended, internal 2.5V reference		54		dB
	pulse Distortion Ra- tio (SNDR)	500 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		56		dB
		500 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		53		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		55		dB
		500 kSamples/s, 12 bit, sin- gle ended, internal 1.25V refer- ence		62		dBc
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		56		dBc
SFDR _{DAC}	Dynamic Range(SFDR)	500 kSamples/s, 12 bit, differ- ential, internal 1.25V reference		61		dBc
		500 kSamples/s, 12 bit, differ- ential, internal 2.5V reference		55		dBc
		500 kSamples/s, 12 bit, differential, V_{DD} reference		60		dBc
V	Offset voltage	After calibration, single ended		2	12	mV
V DACOFFSET	Oliset voltage	After calibration, differential		2		mV
DNL _{DAC}	Differential non-lin- earity			±1		LSB
INL _{DAC}	Integral non-lineari- ty			±5		LSB
MC _{DAC}	No missing codes			12		bits

¹Measured with a static input code and no loading on the output.

3.12 Operational Amplifier (OPAMP)

The electrical characteristics for the Operational Amplifiers are based on simulations.

Table 3.16. OPAMP

Symbol	Parameter	Condition	Min	Тур	Мах	Unit
I _{OPAMP}	Active Current	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, Unity Gain		350	405	μA
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, Unity Gain		95	115	μA

3.13 Analog Comparator (ACMP)

Table 3.17. ACMP

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{ACMPIN}	Input voltage range		0		V _{DD}	V
V _{ACMPCM}	ACMP Common Mode voltage range		0		V _{DD}	V
	Active current	BIASPROG=0b0000, FULL- BIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		0.1	0.6	μA
Symbol Vacmpin Vacmpcm Iacmp Iacmp Vacmpoffset Vacmpoffset Rcsres		BIASPROG=0b1111, FULL- BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.87	12	μA
		BIASPROG=0b1111, FULL- BIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		250	520	μA
IACMPREF	Current consump- tion of internal volt- age reference	Internal voltage reference off. Using external voltage refer- ence		0		μA
		Internal voltage reference		5		μA
VACMPOFFSET	Offset voltage	BIASPROG= 0b1010, FULL- BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
V _{ACMPHYST}	ACMP hysteresis	Programmable		17		mV
R _{CSRES}	Capacitive Sense Internal Resistance	CSRESSEL=0b00 in ACMPn_INPUTSEL		43		kOhm
		CSRESSEL=0b01 in ACMPn_INPUTSEL		78		kOhm
		CSRESSEL=0b10 in ACMPn_INPUTSEL		111		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		145		kOhm
t _{ACMPSTART}	Startup time				10	μs

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 43). $I_{ACMPREF}$ is zero if an external voltage reference is used.

Total ACMP Active Current

 $I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF}$

(3.1)

3.18 Digital Peripherals

Table 3.24. Digital Peripherals

Symbol	Parameter	Condition	Min	Тур	Max	Unit
I _{USART}	USART current	USART idle current, clock en- abled		4.9		μΑ/ MHz
I _{UART}	UART current	UART idle current, clock en- abled		3.4		μΑ/ MHz
I _{LEUART}	LEUART current	LEUART idle current, clock en- abled		140		nA
I _{I2C}	I2C current	I2C idle current, clock enabled		6.1		µA/ MHz
I _{TIMER}	TIMER current	TIMER_0 idle current, clock enabled		6.9		µA/ MHz
I _{LETIMER}	LETIMER current	LETIMER idle current, clock enabled		119		nA
I _{PCNT}	PCNT current	PCNT idle current, clock en- abled		54		nA
I _{RTC}	RTC current	RTC idle current, clock enabled		54		nA
I _{AES}	AES current	AES idle current, clock enabled		3.2		μΑ/ MHz
I _{GPIO}	GPIO current	GPIO idle current, clock en- abled		3.7		µA/ MHz
I _{PRS}	PRS current	PRS idle current		3.5		μΑ/ MHz
I _{DMA}	DMA current	Clock enable		11.0		μΑ/ MHz

5 PCB Layout and Soldering

5.1 Recommended PCB Layout

Figure 5.1. TQFP64 PCB Land Pattern



Table 5.1. QFP64 PCB Land Pattern Dimensions (Dimensions in mm)

Symbol	Dim. (mm)	Symbol	Pin number	Symbol	Pin number
а	1.60	P1	1	P6	48
b	0.30	P2	16	P7	49
с	0.50	P3	17	P8	64
d	11.50	P4	32	-	-
е	11.50	P5	33	-	-

A Disclaimer and Trademarks

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List of Equations

3.1. Total ACMP Active Current	43
3.2. VCMP Trigger Level as a Function of Level Setting	45